



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-363 Plastic-Encapsulate Transistors

SD103ATW

SWITCHING DIODE

SOT-363



FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^{\circ}C$)

Collector current

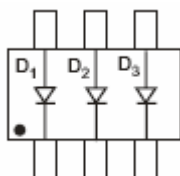
I_O : 175 mA

Collector-base voltage

V_R : 40 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



MARKING:KLL

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$	40		V
Reverse voltage leakage current	I_R	$V_R=10V$ $V_R=30V$		2 5	μA
Forward voltage	V_F	$I_F=1mA$ $I_F=5mA$ $I_F=20mA$ $I_F=100mA$		0.27 0.32 0.37 0.50	V
Total capacitance	C_T	$V_R=0V$ $f=1MHz$		50	pF
Reveres recovery time	t_{rr}	$I_F=I_R=200mA$ $I_{rr}=0.1 \times I_R, R_L=100 \Omega$		10	nS